

## **IN THE SPECIFICATION**

Please replace the abstract with the following:

### **ABSTRACT OF THE DISCLOSURE**

~~A method for providing substantially similar chamber condition before each wafer process operation in a semiconductor process chamber is provided. The method allows for prevention of transport of particle and metal contamination from chamber surfaces to the processed wafer. The method initiates with depositing a silicon containing layer over an inner surface of an empty semiconductor process chamber. Then, a wafer is introduced into the semiconductor process chamber after depositing the silicon containing layer. Next, a process operation is performed on the wafer. The process operation deposits a residue on the silicon containing layer. Next, an in-situ cleaning process is initiated upon completion of the processing operation and removal of the wafer. The process initiation includes flowing a fluorine containing gas into the semiconductor process chamber, and establishing a pressure within the semiconductor process chamber capable of allowing a plasma created from the fluorine containing gas to clear the silicon containing layer covering the inner surface of the processing chamber. A semiconductor processing chamber having a silicon containing pre-coat is also provided. The chamber includes a top electrode in communication with a power supply and a processing chamber defined within a base, a sidewall extending from the base, and a top disposed on the sidewall. The processing chamber has an outlet enabling removal of fluids within the processing chamber and includes a substrate support where an outer surface of the substrate support coated with the removable silicon containing coating, wherein the silicon containing coating is a compound consisting essentially of silicon and one of~~

bromine and chlorine. The chamber includes an inner surface o defined by the base,  
the sidewall and the top, where the inner surface is coated with a removable silicon  
containing coating. The silicon containing coating is configured to seal particles  
between the inner surface and the silicon containing coating.